

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	6.4mΩ@10V	90A
	8.4mΩ@4.5V	



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

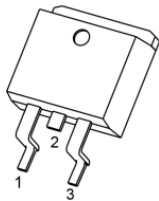
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Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test
- Power switching application
- DC-DC Converter
- Power Management

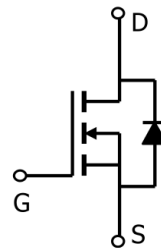
Applications

Package

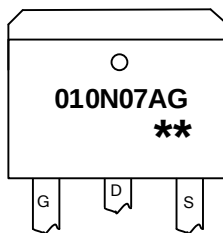


TO-263(G:1 D:2 S:3)

Circuit diagram



Marking



010N07AG : Product code
** : Week code

Order Information

Device	Package	Unite/Tape
SP010N07AGTD	TO-263-3L	800

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current (Tc=25°C)	I_D	90	A
Pulsed drain current	I_{DM}	360	A
Power dissipation (Tc=25°C)	P_D	130	W
Single pulsed avalanche energy ¹⁾	E_{AS}	358	mJ
Thermal resistance, junction-case	$R_{\theta JC}$	0.96	°C/W
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

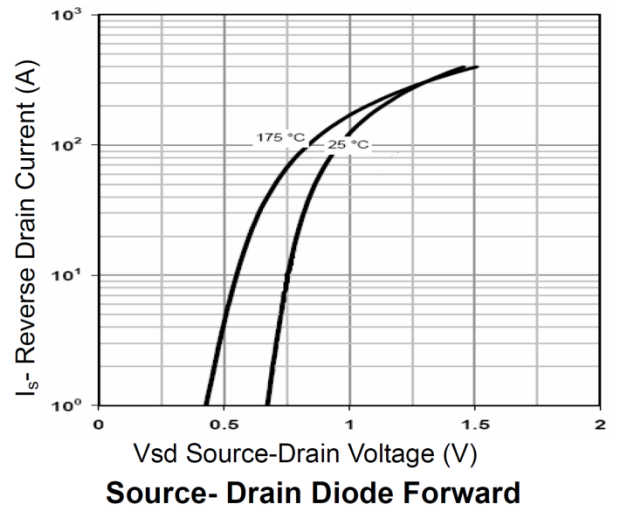
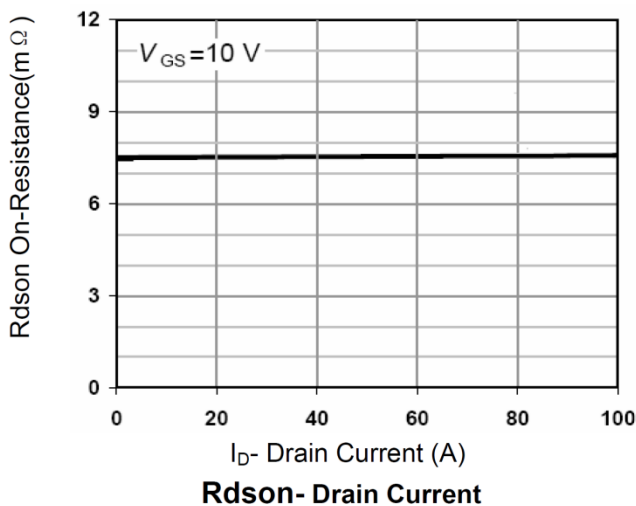
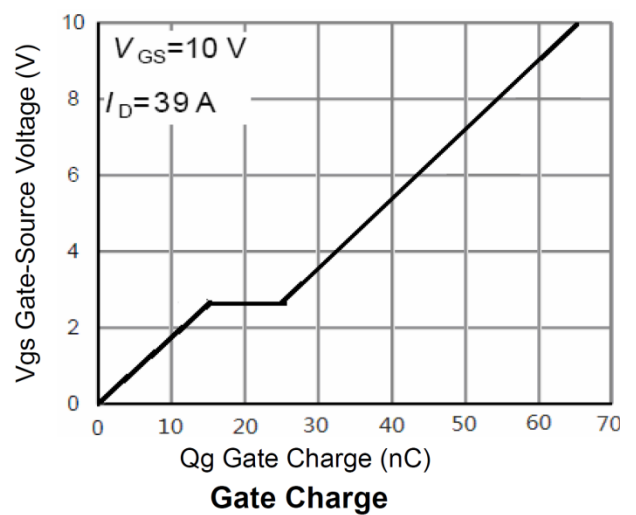
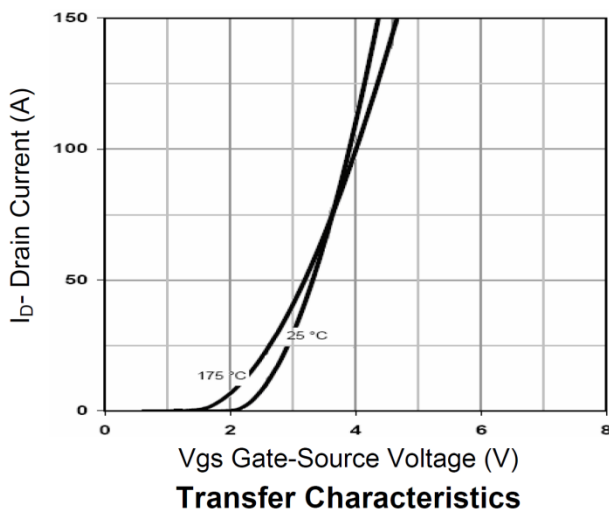
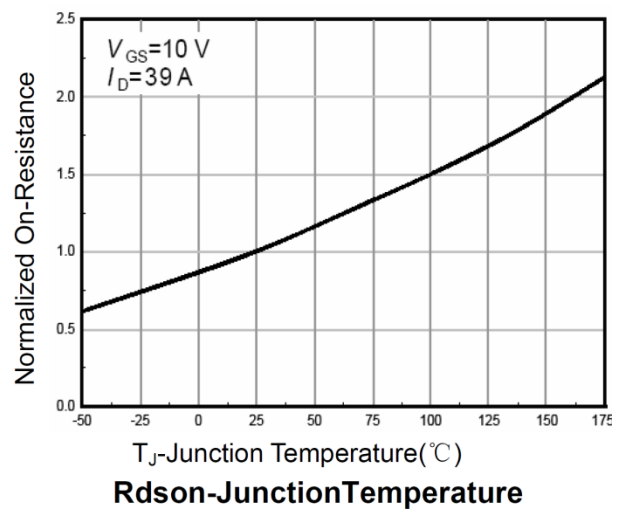
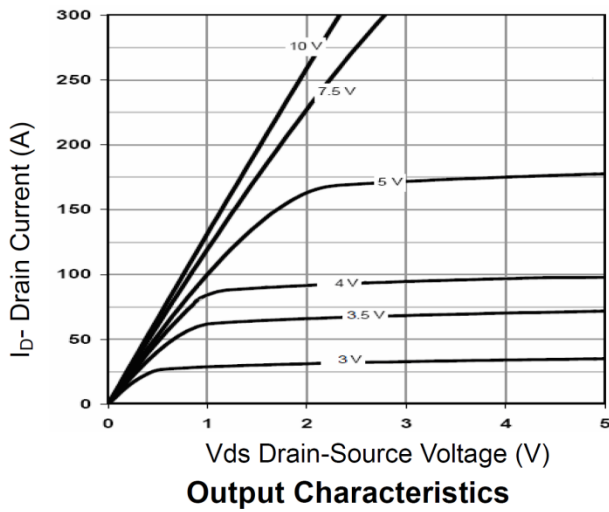
Electrical characteristics (Ta=25°C, unless otherwise noted)

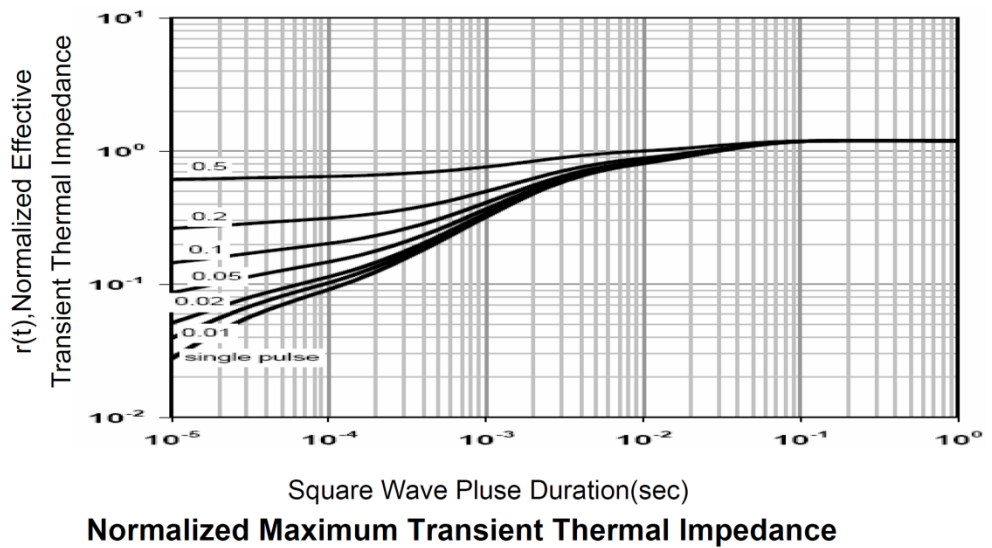
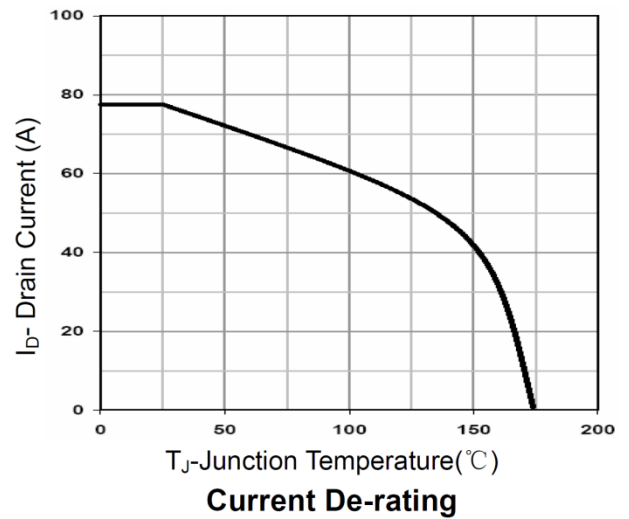
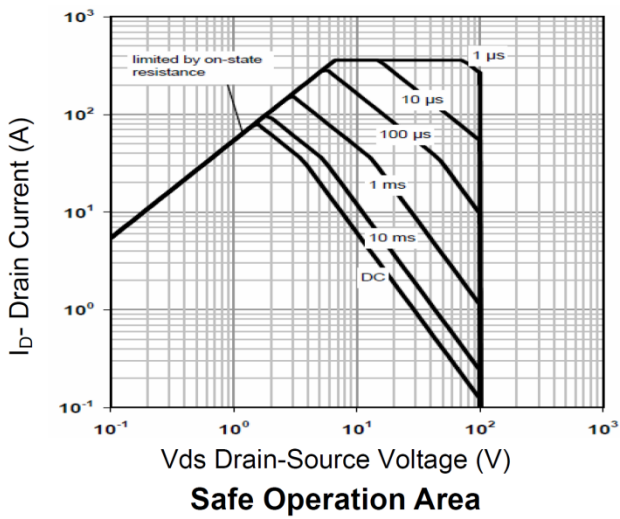
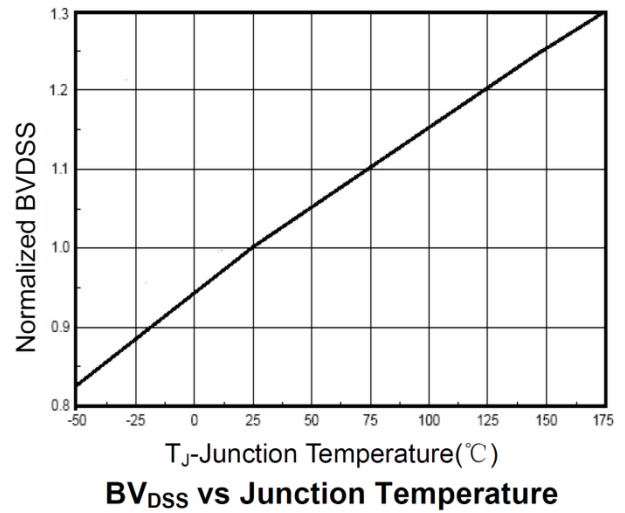
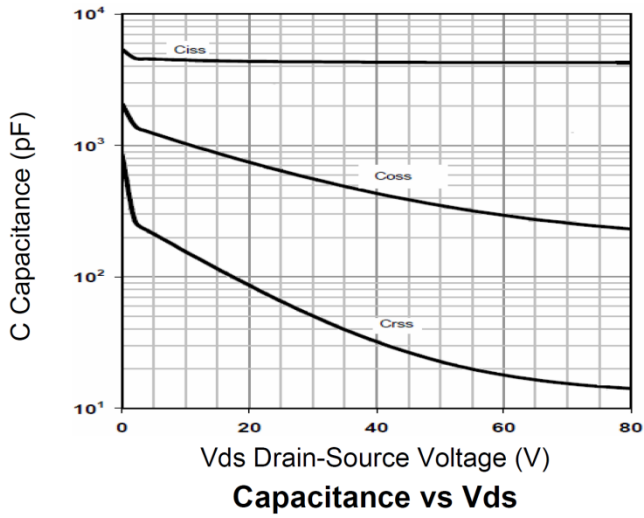
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	100	-	-	V
Drain Cut-Off Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.7	2.5	V
Drain-Source ON Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 30A	-	6.4	8	mΩ
		V _{GS} = 4.5V, I _D = 25A	-	8.4	11.5	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} = 0V, f = 1.0MHz	-	1942	-	pF
Output Capacitance	C _{oss}		-	388	-	
Reverse Transfer Capacitance	C _{rss}		-	12	-	
Switching Characteristics						
Total Gate Charge	Q _g	V _D S=50V , V _G S=10V , I _D =30A	-	67	-	nC
Gate-Source Charge	Q _{gs}		-	12	-	
Gate-Drain Charge	Q _{gd}		-	21	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 50V, R _L =2.5Ω , R _G = 6.0Ω	-	12	-	ns
Rise Time	t _r		-	11	-	
Turn-Off Delay Time	t _{d(off)}		-	42	-	
Fall Time	t _f		-	6	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V

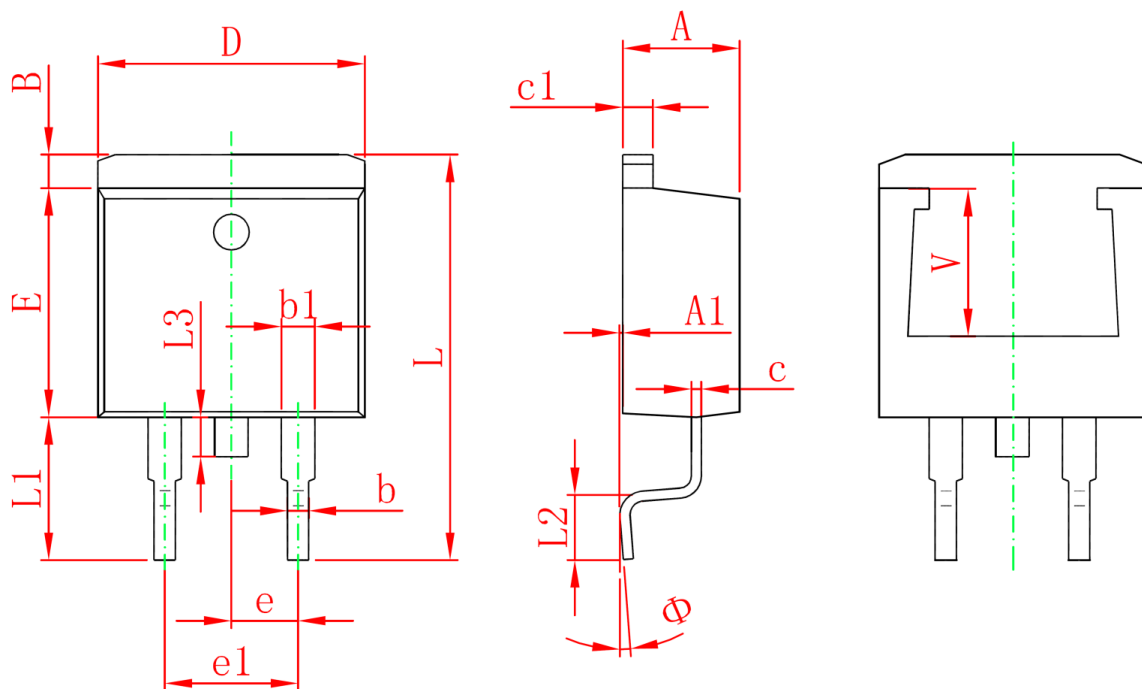
Note:

- E_{AS} is tested at starting $T_j = 25^\circ C$, $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_g = 25m\Omega$;

Typical Characteristics





TO-263 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220 REF.	